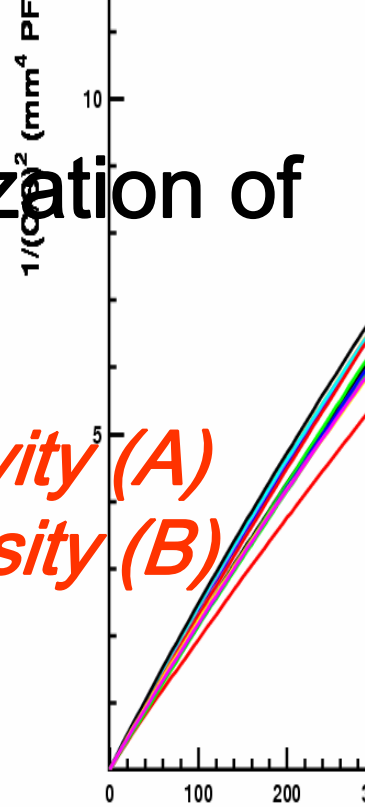


- Pre-irradiation: full electrical characterization of all structures

Uniform wafer resistivity (A)
Uniform Current Density (B)



- Post-irradiation:
 - IV and CV measuremen (at 0 °C or 20 °C) before annealing
 - Measurements repeated after annealing to study evolution on bulk current and effective carrier lifetime
 - Microscopic defect analysis: transmission electron microscopy

Improved annealing

Current related damage

$$\alpha = (\Delta I/V) / \Phi$$

(Extracted at the equivalent annealing @ 60 °C)